

MOS FIELD EFFECT TRANSISTOR μ PA677TB

N-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The μ PA677TB is a switching device which can be driven directly by a 2.5 V power source.

The μ PA677TB features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- 2.5 V drive available
- · Low on-state resistance

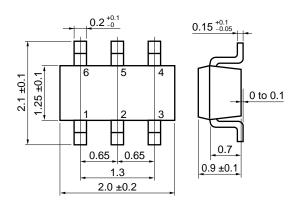
RDS(on)1 = 0.57Ω MAX. (Vgs = 4.5 V, ID = 0.30 A)

RDS(on)2 = 0.60Ω MAX. (Vgs = 4.0 V, ID = 0.30 A)

RDS(on)3 = 0.88Ω MAX. (Vgs = 2.5 V, ID = 0.15 A)

• Two MOS FET circuits in same size package as SC-70

PACKAGE DRAWING (Unit: mm)



ORDERING INFORMATION

PART NUMBER	PACKAGE
μPA677TB	SC-88 (SSP)

Marking: WA

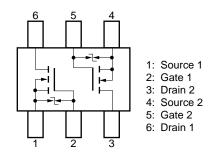
ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vss = 0 V)	VDSS	20	V
Gate to Source Voltage (Vps = 0 V)	Vgss	±12	V
Drain Current (DC)	$I_{D(DC)}$	±0.35	Α
Drain Current (pulse) Note1	I _{D(pulse)}	±1.40	Α
Total Power Dissipation(2units) Note2	Рт	0.2	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

2. Mounted on FR-4 Board of 2500 mm² x 1.1 mm 2units total.

PIN CONNECTUON (Top View)



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

Caution This product is electrostatic-sensitive device due to low ESD capability and should be handled with caution for electrostatic discharge.

VESD = ± 200 V TYP. (C = 200 pF, R = 0 Ω , Single pulse)

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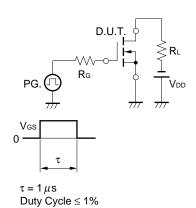


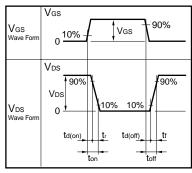
ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	Ipss	V _{DS} = 20.0 V, V _{GS} = 0 V			1.0	μΑ
Gate Leakage Current	Igss	V _G S = ±12.0 V, V _D S = 0 V			±10	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10.0 V, I _D = 1.0 mA	0.5	1.0	1.5	٧
Forward Transfer Admittance ^{Note}	yfs	V _{DS} = 10.0 V, I _D = 0.30 A	0.25	0.75		S
Drain to Source On-state Resistance Note	RDS(on)1	V _G S = 4.5 V, I _D = 0.30 A		0.38	0.57	Ω
	R _{DS(on)2}	V _{GS} = 4.0 V, I _D = 0.30 A		0.41	0.60	Ω
	RDS(on)3	Vgs = 2.5 V, ID = 0.15 A		0.60	0.88	Ω
Input Capacitance	Ciss	V _{DS} = 10.0 V		28		рF
Output Capacitance	Coss	V _{GS} = 0 V		11		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		7		pF
Turn-on Delay Time	td(on)	V _{DD} = 10.0 V, I _D = 0.30 A		20		ns
Rise Time	tr	V _{GS} = 4.0 V		51		ns
Turn-off Delay Time	td(off)	R _G = 10 Ω		94		ns
Fall Time	t f			87		ns
Body Diode Forward Voltage Note	VF(S-D)	IF = 0.35 A, VGS = 0 V		0.84		V

Note Pulsed PW \leq 350 μ s, Duty Cycle \leq 2%

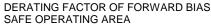
TEST CIRCUIT SWITCHING TIME

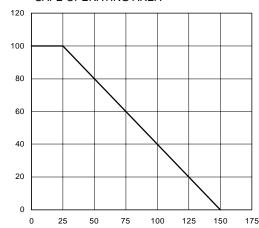




dT - Percentage of Rated Power - %

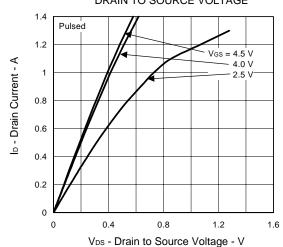
TYPICAL CHARACTERISTICS (TA = 25°C)



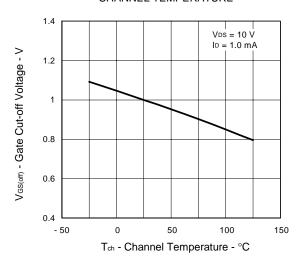


T_A - Ambient Temperature - °C

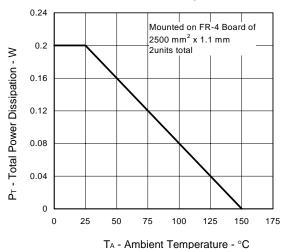
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



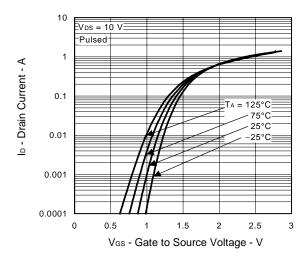
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



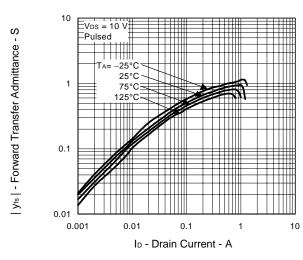
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



FORWARD TRANSFER CHARACTERISTICS



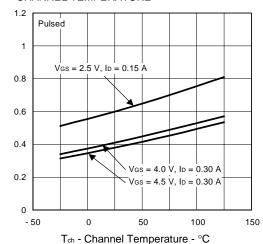
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



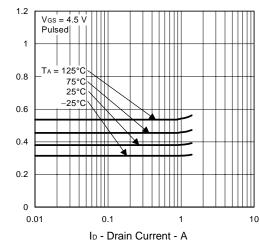
 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ - Drain to Source On-state Resistance - Ω

 $\mathsf{Ros}_\text{(on)}$ - Drain to Source On-state Resistance - Ω

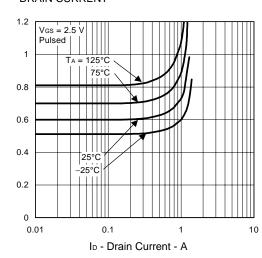
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



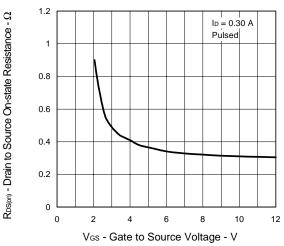
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



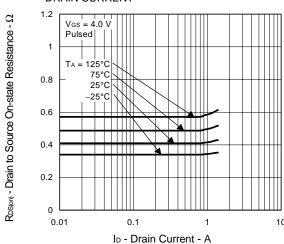
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



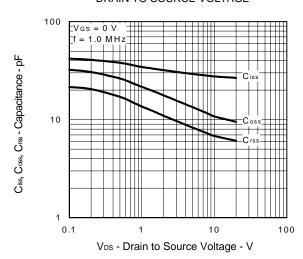
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



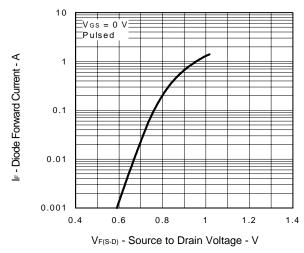
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



R_{DS(on)} - Drain to Source On-state Resistance - Ω

SWITCHING CHARACTERISTICS 1000 VDD = 10 V VGS = 4.0 V RG = 10 Ω RG = 10 Ω td(off) 100 10 0.01 0.1 1 10 Ib - Drain Current - A

SOURCE TO DRAIN DIODE FORWARD VOLTAGE



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